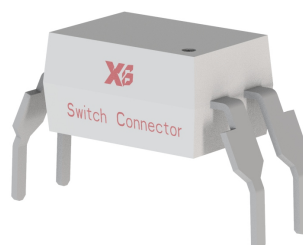
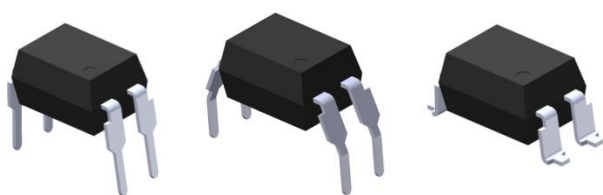
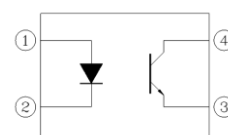


4 PIN DIP LOW INPUT PHOTOTRANSISTOR PHOTOCOUPLER EL8171-G Series



Schematic



Features:

- Current transfer ratio
(CTR: 100~350% at $I_F = 0.5\text{mA}$, $V_{CE} = 5\text{V}$)
- High isolation voltage between input and output (Viso = 5000Vrms)
- Creepage distance > 7.62 mm
- Operating temperature up to +100°C
- Compliance with EU REACH
- Compliance Halogen Free (Br < 900ppm, Cl < 900ppm, Br+Cl < 1500ppm)
- The product itself will remain within RoHS compliant version
- UL and cUL approved (No. E214129)
- VDE approved (No. 132249)
- CQC approved

Pin Configuration

1. Anode
2. Cathode
3. Emitter
4. Collector

Description

The EL8171-G series of devices each consist of an infrared emitting diodes, optically coupled to a phototransistor detector with green compound.

They are packaged in a 4-pin DIP package and available in wide-lead spacing and SMD option.

Applications

- Programmable controllers
- System appliances, measuring instruments
- Telecommunication equipments
- Home appliances, such as fan heaters, etc.
- Signal transmission between circuits of different potentials and impedances

Absolute Maximum Ratings (Ta=25°C)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I_F	10	mA
	Reverse voltage	V_R	6	V
	Power dissipation	P_D	20	mW
Output	Power dissipation	P_C	150	mW
	Collector current	I_C	50	mA
	Collector-Emitter voltage	V_{CEO}	70	V
	Emitter-Collector voltage	V_{ECO}	6	V
Total power dissipation		P_{TOT}	170	mW
Isolation voltage *1		V_{ISO}	5000	V rms
Operating temperature		T_{OPR}	-30 ~ +100	°C
Storage temperature		T_{STG}	-55 ~ +125	°C
Soldering Temperature*2		T_{SOL}	260	°C

Notes:

*1 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1 & 2 are shorted together, and pins 3 & 4 are shorted together.

*2 For 10 seconds

Electro-Optical Characteristics (Ta=25°C unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Forward Voltage	V_F	-	1.2	1.4	V	$I_F = 10\text{mA}$
Reverse Current	I_R	-	-	10	μA	$V_R = 4\text{V}$
Input capacitance	C_{in}	-	-	250	pF	$V = 0, f = 1\text{kHz}$

Output

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Collector-Emitter dark current	I_{CEO}	-	-	100	nA	$V_{CE} = 20\text{V}, I_F = 0\text{mA}$
Collector-Emitter breakdown voltage	BV_{CEO}	70	-	-	V	$I_C = 0.1\text{mA}$
Emitter-Collector breakdown voltage	BV_{ECO}	6	-	-	V	$I_E = 0.1\text{mA}$

Transfer Characteristics

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Current Transfer ratio	CTR	100	-	350	%	$I_F = 0.5\text{mA}, V_{CE} = 5\text{V}$
Collector-Emitter saturation voltage	$V_{CE(sat)}$	-	--	0.2	V	$I_F = 10\text{mA}, I_C = 1\text{mA}$
Isolation resistance	R_{IO}	5×10^{10}	-	-	Ω	$V_{IO} = 500\text{Vdc}, 40\sim60\% \text{ R.H.}$
Floating capacitance	C_{IO}	-	-	1.0	pF	$V_{IO} = 0, f = 1\text{MHz}$
Cut-off frequency	f_c	-	80	-	kHz	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$ $R_L = 100\Omega, -3\text{dB}$
Rise time	t_r	-	-	18	μs	$V_{CE} = 2\text{V}, I_C = 2\text{mA}, R_L = 100\Omega$
Fall time	t_f	-	-	18	μs	

* Typical values at $T_a = 25^\circ\text{C}$

Typical Electro-Optical Characteristics Curves

Figure 1. Forward Current vs Forward Voltage

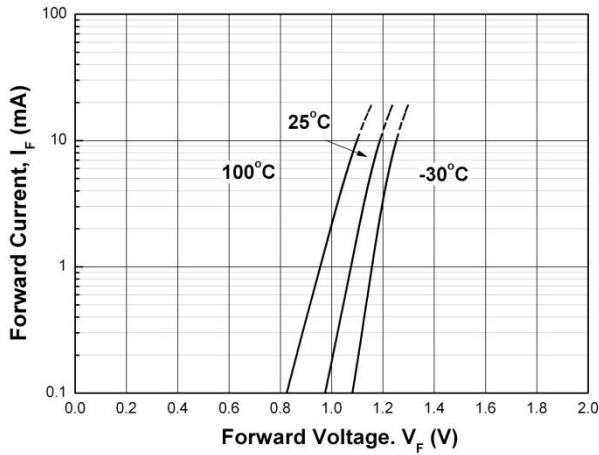


Figure 2. Normalized Current Transfer Ratio vs Forward Current

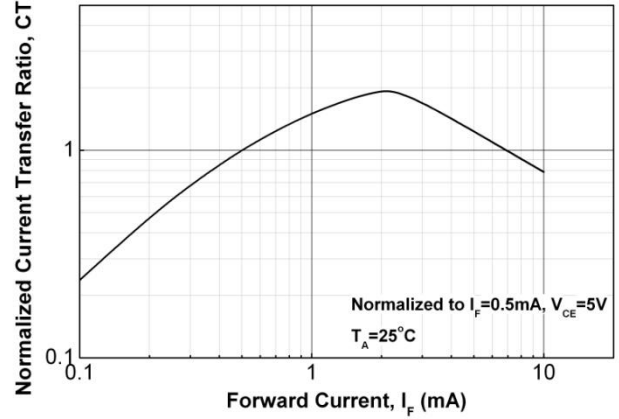


Figure 3. Current Transfer Ratio vs Ambient Temperature

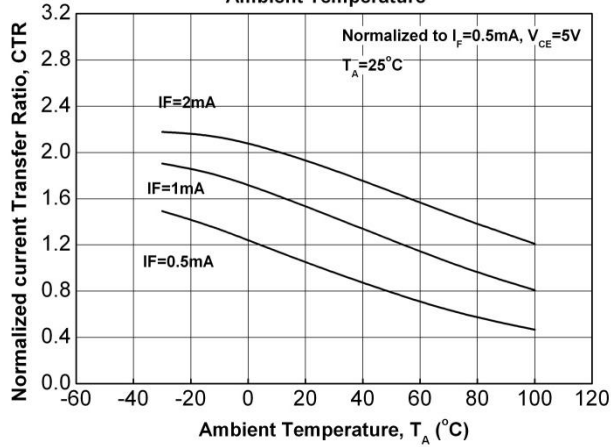


Figure 4. Dark Current vs Ambient Temperature

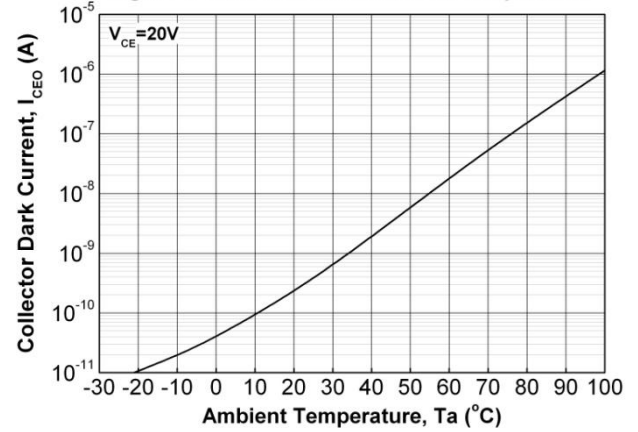


Figure 5. Collector Current vs. Collector Emitter Voltage

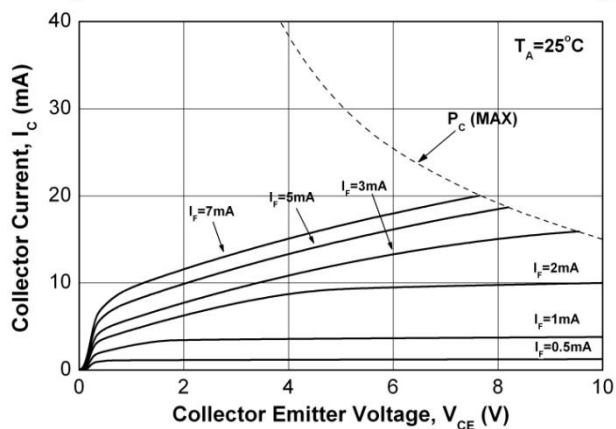
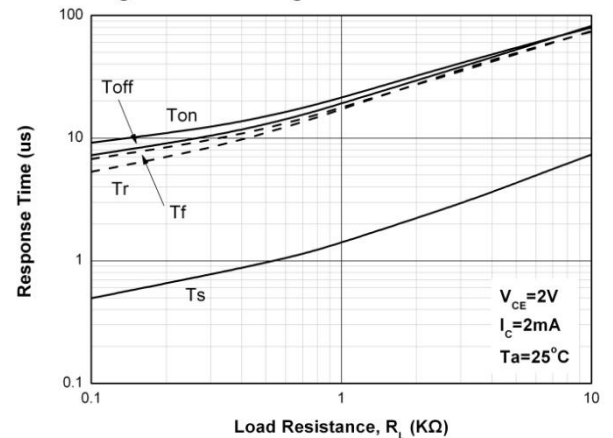


Figure 6. Switching Time vs. Load Resistance



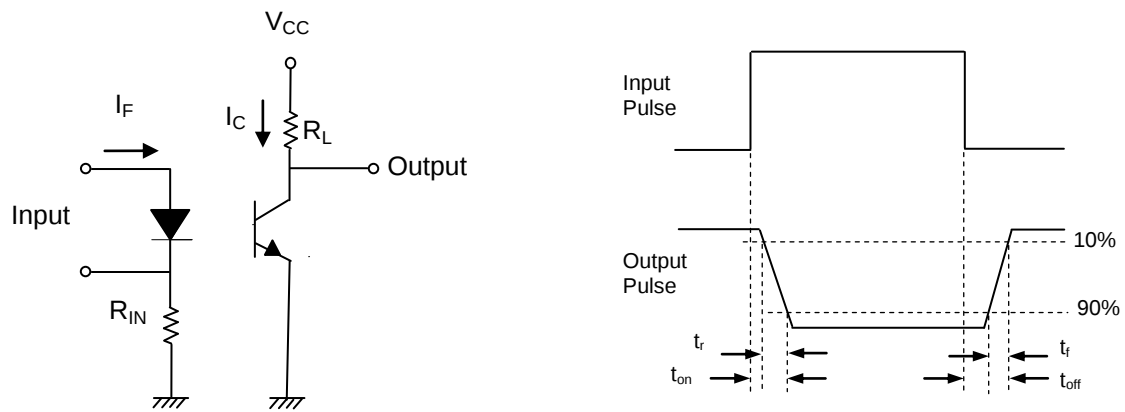


Figure 7. Switching Time Test Circuit & Waveforms

Order Information

Part Number

EL8171X(Z)-VG

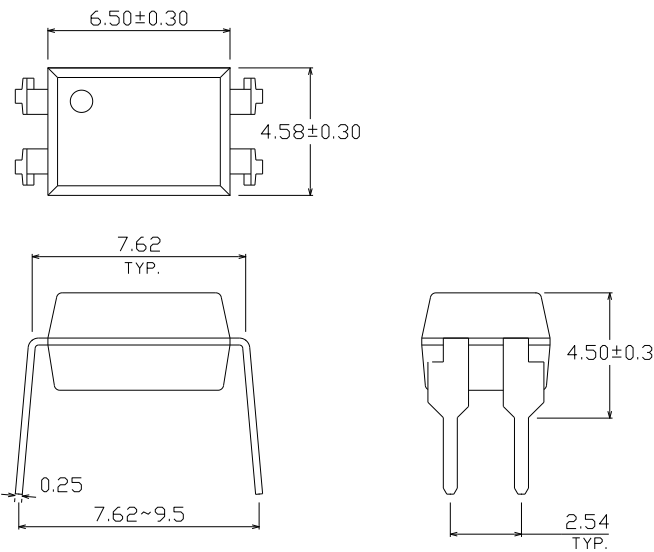
Note

- X = Lead form option (S, S1, M or none)
Z = Tape and reel option (TA, TB ,TU, TD or none)
V = VDE safety (optional)
G = Halogens free

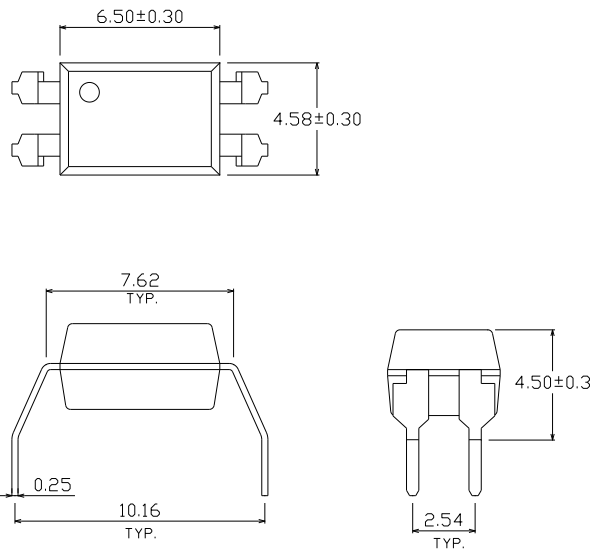
Option	Description	Packing quantity
None	Standard DIP-4	100 units per tube
M	Wide lead bend (0.4 inch spacing)	100 units per tube
S (TA)	Surface mount lead form + TA tape & reel option	1000 units per reel
S (TB)	Surface mount lead form + TB tape & reel option	1000 units per reel
S1 (TA)	Surface mount lead form (low profile) + TA tape & reel option	1000 units per reel
S1 (TB)	Surface mount lead form (low profile) + TB tape & reel option	1000 units per reel
S (TU)	Surface mount lead form + TU tape & reel option	1500 units per reel
S (TD)	Surface mount lead form + TD tape & reel option	1500 units per reel
S1 (TU)	Surface mount lead form (low profile) + TU tape & reel option	1500 units per reel
S1 (TD)	Surface mount lead form (low profile) + TD tape & reel option	1500 units per reel

Package Dimension (Dimensions in mm)

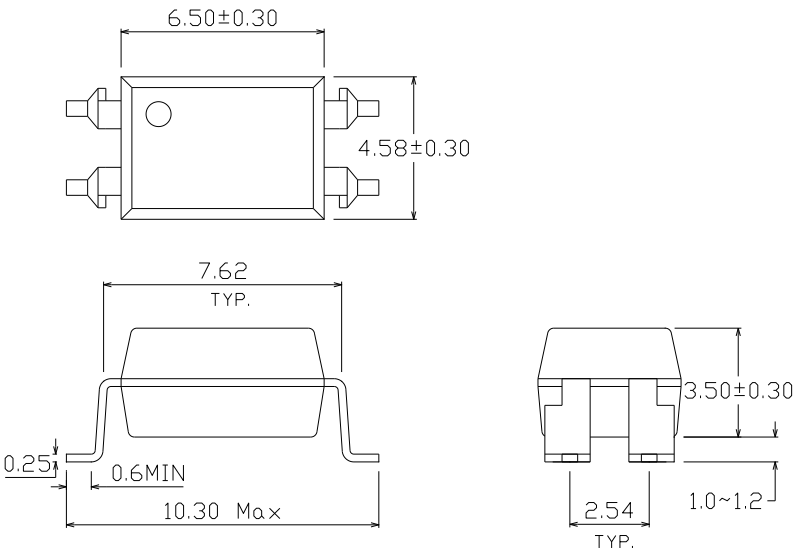
Standard DIP Type



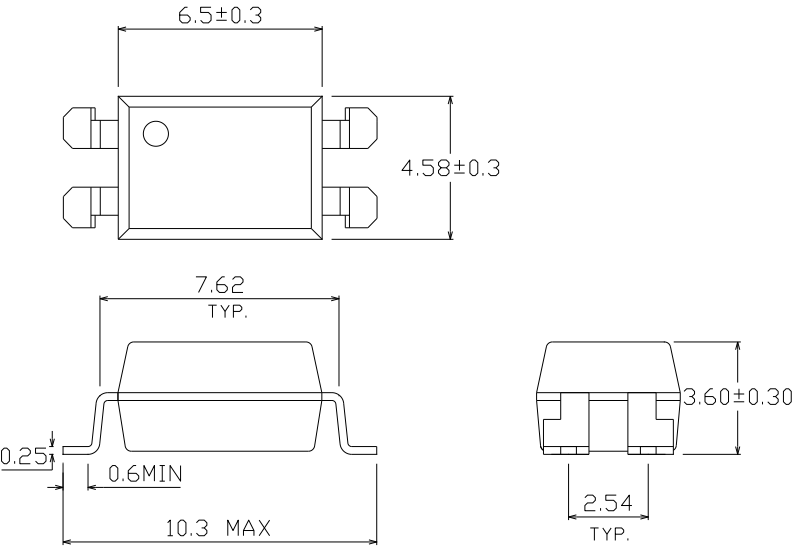
Option M Type



Option S Type

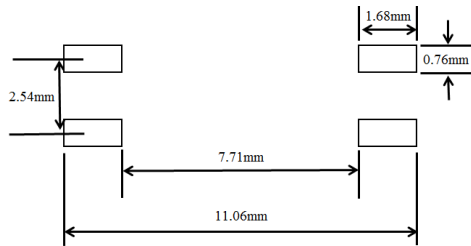


Option S1 Type

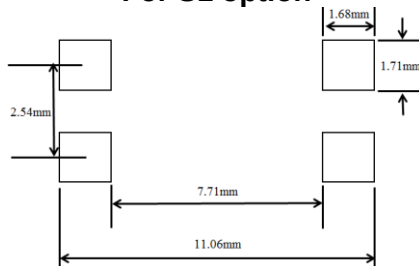


Recommended pad layout for surface mount leadform

For S option



For S1 option



Notes

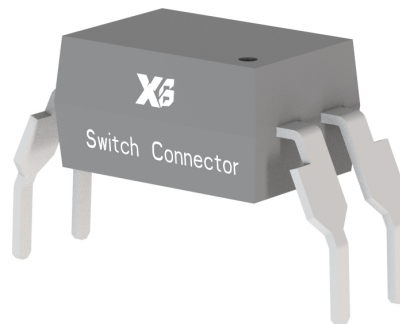
Suggested pad dimension is just for reference only.
Please modify the pad dimension based on individual need.

Device Marking

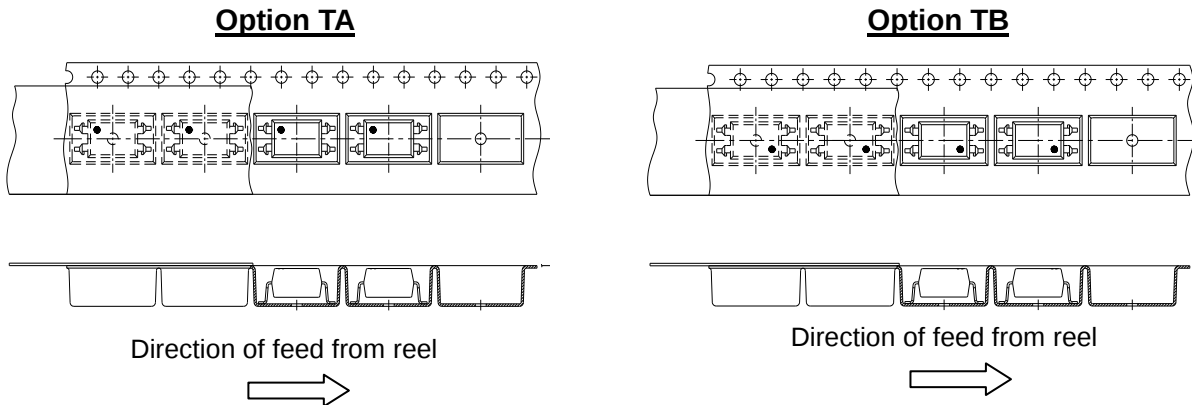


Notes

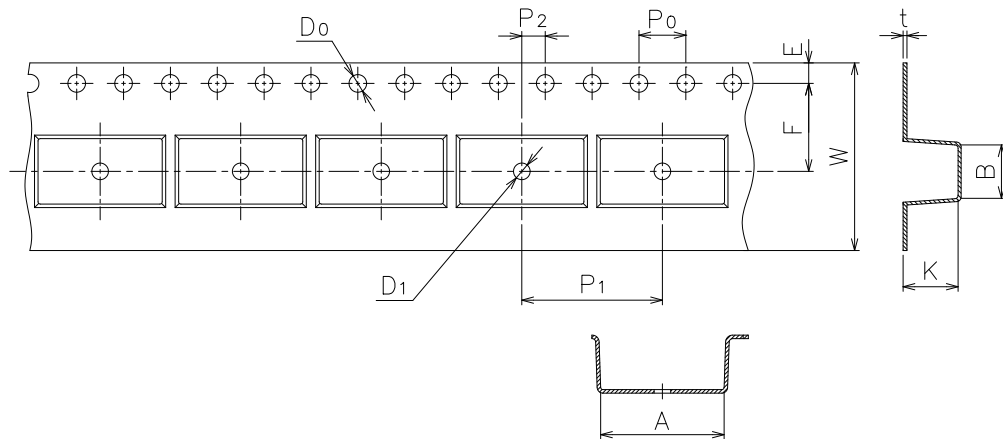
EL denotes XI BNANG
8171 denotes Device Number
G denotes Green part
Y denotes 1 digit Year code WW
denotes 2 digit Week code
V denotes VDE optional



Tape & Reel Packing Specifications

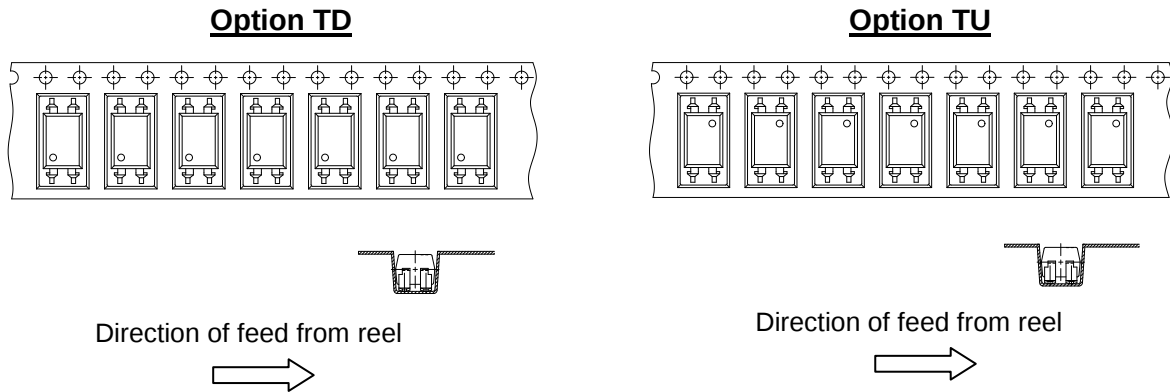


Tape dimensions

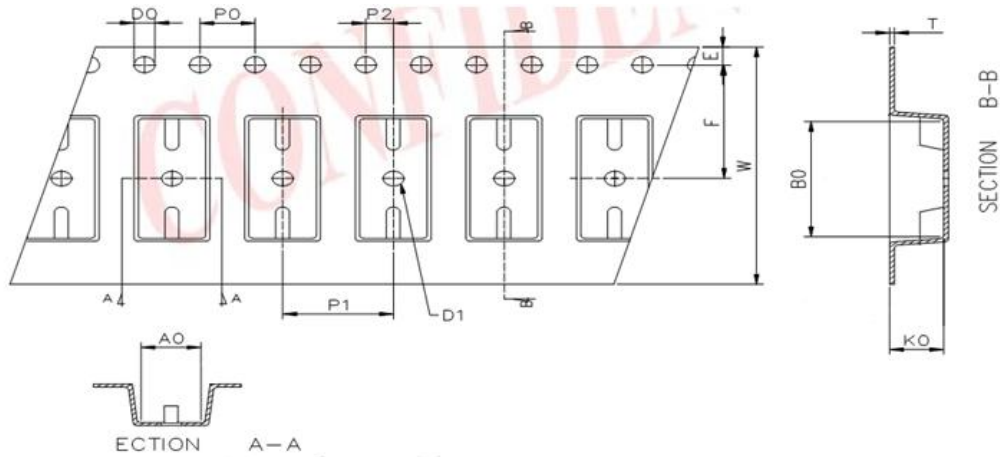


Dimension No.	A	B	D ₀	D ₁	E	F
Dimension (mm) S	10.7±0.1	4.65±0.1	1.5±0.1	1.50±0.1	1.75±0.1	7.5±0.1
Dimension (mm) S1	10.7±0.1	4.65±0.1	1.5±0.1	1.50±0.1	1.75±0.1	7.5±0.1
Dimension No.	P ₀	P ₁	P ₂	t	W	K
Dimension (mm) S	4.0±0.1	12.0±0.1	2.0±0.1	0.4±0.1	16.0±0.3	4.75±0.1
Dimension (mm) S1	4.0±0.1	12.0±0.1	2.0±0.1	0.4±0.1	16.0±0.3	3.90±0.1

Tape & Reel Packing Specifications



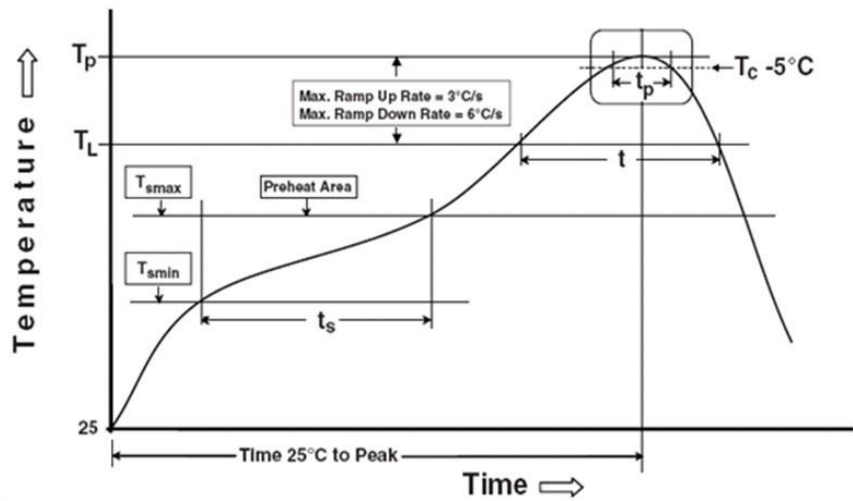
Tape dimensions



Dimension No.	Ao	Bo	Do	D1	E	F
Dimension(mm)	4.90±0.1	10.40±0.1	1.5±0.1	1.50±0.1	1.75±0.1	7.50±0.1
Dimension No.	Po	P1	P2	t	W	Ko
Dimension(mm)	4.00±0.1	8.00±0.1	2.00±0.1	0.40±0.1	16.00±0.3	4.60±0.1

Precautions for Use

- 1. Soldering Condition
 - 1.1 (A) Maximum Body Case Temperature Profile for evaluation of Reflow Profile



Note: Reference: IPC/JEDEC J-STD-020D

Preheat

Temperature min (T_{smin})	150 °C
Temperature max (T_{smax})	200°C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max

Other

Liquidus Temperature (T_L)	217 °C
Time above Liquidus Temperature (t_L)	60-100 sec
Peak Temperature (T_P)	260°C
Time within 5 °C of Actual Peak Temperature: $T_P - 5^\circ\text{C}$	30 s
Ramp- Down Rate from Peak Temperature	6°C /second max
Time 25°C to peak temperature	8 minutes max
Reflow times	3 times

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2. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
3. When using this product, please observe the absolute maximum ratings and the instructions for use outlined in these specification sheets. XI BNANG assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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